

JC868 U.S. PTO  
10/073506  
02/11/02

5C/900  
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U.S. UTILITY Patent Application

PATENT NUMBER and  
ISSUE DATE

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10073506	02/11/2002	429	446	1775	S. J. J.

\*\*APPLICANTS: Falster Robert; Binns Martin; Wang Alan;

\*\*CONTINUING DATA VERIFIED:

THIS APPLICATION IS A DIV OF 09/416,998 10/13/1999  
WHICH CLAIMS BENEFIT OF 60/104,304 10/14/1993

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\*\* FOREIGN APPLICATIONS VERIFIED:

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no		ATTORNEY DOCKET NO
35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no		MEMO 98-1451/2554.1
Verified and Acknowledged Examiners's initials		
TITLE : Thermal annealing process for producing low defect density single crystal silicon		
U.S. DEPT. OF COMM./PAT. & TM.-PTO-436L (Rev. 12-94)		

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G.
Assistant Examiner		DRAWING	
		Sheets Drwg.	Figs. Drwg.
Amount Due		Print Fig.	
Date Paid			
Primary Examiner		Application Examiner	
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE	
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